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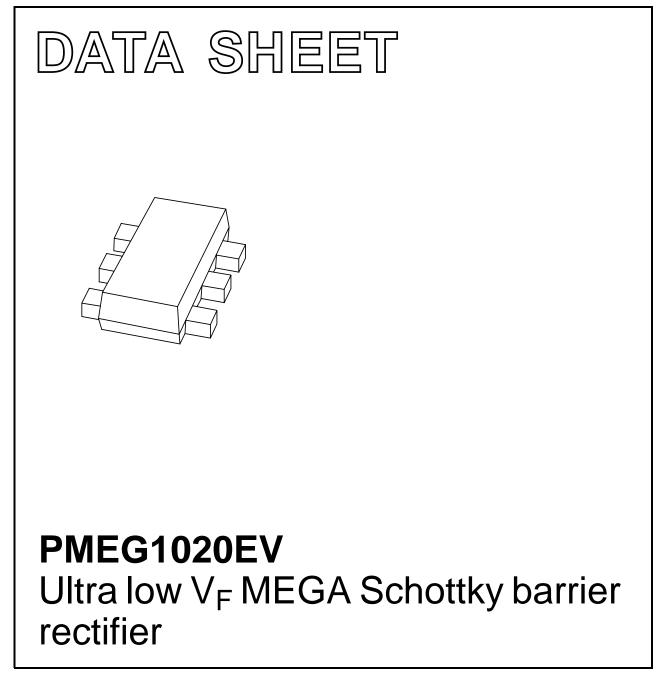
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Kind regards,

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DISCRETE SEMICONDUCTORS



Product data sheet

2003 Jul 15



Product data sheet

Ultra low V_F MEGA Schottky barrier rectifier

FEATURES

- Forward current: 2 A
- Reverse voltage: 10 V
- Ultra low forward voltage
- Ultra small plastic SMD package.

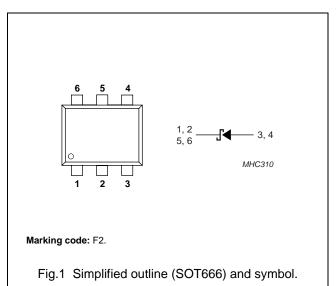
APPLICATIONS

- Low voltage rectification
- High efficiency DC/DC conversion
- Switch mode power supply
- · Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOT666 ultra small plastic SMD package.

| PINNING | | | |
|---------|-------------|--|--|
| PIN | DESCRIPTION | | |
| 1 | cathode | | |
| 2 | cathode | | |
| 3 | anode | | |
| 4 | anode | | |
| 5 | cathode | | |
| 6 | cathode | | |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|---|------|------|------|
| V _R | continuous reverse voltage | | - | 10 | V |
| I _F | continuous forward current | $T_{sp} \le 55 \ ^{\circ}C$; note 1 | - | 2 | А |
| I _{FRM} | repetitive peak forward current | $t_p \le 1 \text{ ms}; \delta \le 0.5; \text{ note } 1$ | - | 3.2 | А |
| I _{FSM} | non-repetitive peak forward current | t _p = 8 ms square wave; note 1 | - | 9 | А |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Only valid if pins 3 and 4 are connected in parallel.

PMEG1020EV

Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|-------------------|--|------|------|------|
| V _F | forward voltage | see Fig.2; note 1 | | | |
| | | I _F = 0.01 A | 100 | 130 | mV |
| | | I _F = 0.1 A | 164 | 200 | mV |
| | | I _F = 1 A | 255 | 350 | mV |
| | | I _F = 2 A | 306 | 460 | mV |
| I _R | reverse current | see Fig.3 note 2 | | | |
| | | V _R = 5 V | 0.7 | 2 | mA |
| | | V _R = 8 V | 1 | 2.5 | mA |
| | | V _R = 10 V | 1.2 | 3 | mA |
| C _d | diode capacitance | V _R = 5 V; f = 1 MHz; see Fig.4 | 37 | 45 | pF |

Notes

- 1. Pulse test: $t_p = 300 \ \mu s$; $\delta = 0.02$.
- 2. For Schottky barrier rectifiers thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | | UNIT |
|---------------------|--|------------|-----|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 405 | K/W |
| | | note 2 | 215 | K/W |
| R _{th j-s} | thermal resistance from junction to solder point | note 3 | 80 | K/W |

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm².
- 3. Solder point of cathode tabs.

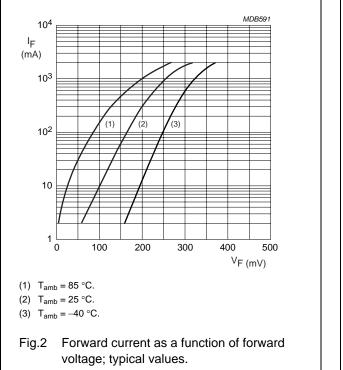
Soldering

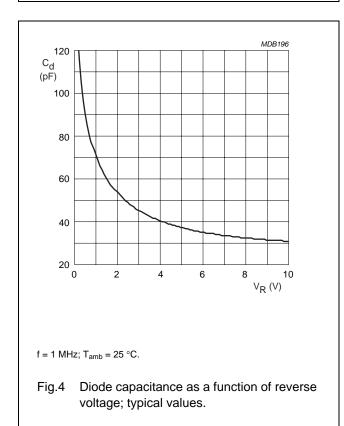
Reflow soldering is the only recommended soldering method.

Ultra low V_F MEGA Schottky barrier rectifier

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GRAPHICAL DATA



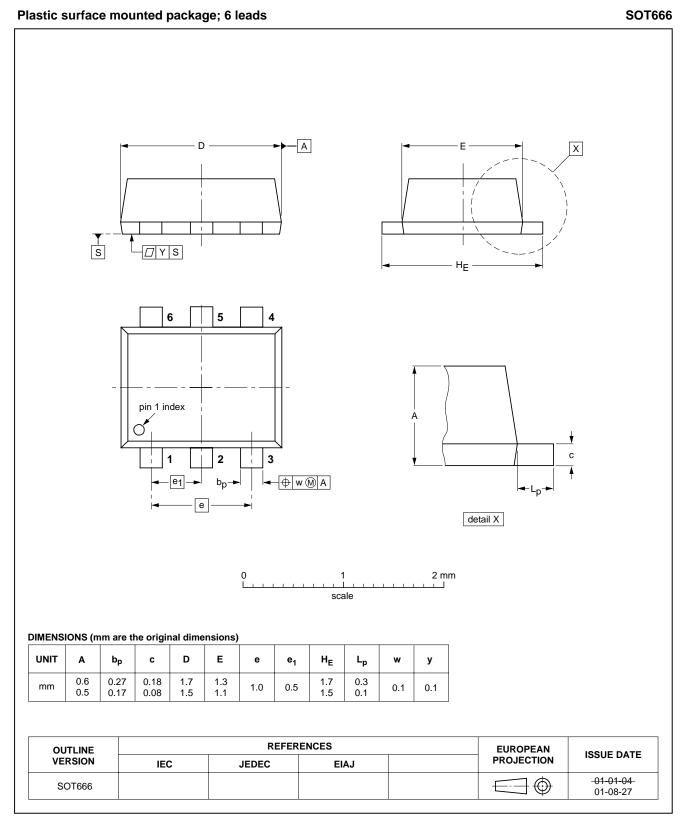


MDB195 10⁵ ^{I}R -(1) (µA) 10⁴ 10³ (2) 10² 10 _(3) 1 2 4 6 8 10 0 $V_{\mathsf{R}}(V)$ (1) T_{amb} = 85 °C. (2) T_{amb} = 25 °C. (3) $T_{amb} = -40 \ ^{\circ}C.$ Fig.3 Reverse current as a function of reverse voltage; typical values.

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Ultra low V_F MEGA Schottky barrier rectifier

PACKAGE OUTLINE



PMEG1020EV

2003 Jul 15

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Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

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Printed in The Netherlands

613514/01/pp7

Date of release: 2003 Jul 15

Document order number: 9397 750 11686

